

Ordering number : ENN7625

P-Channl Silicon MOSFET

2SJ652

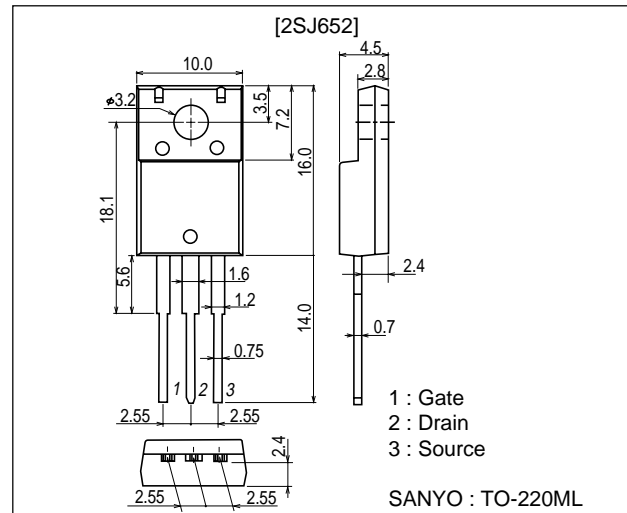
General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.
- Motor drive, DC / DC converter.

Package Dimensions

unit : mm
2063A



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-60	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		-28	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-112	A
Allowable Power Dissipation	P _D		2.0	W
		T _c =25°C	30	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =-1mA, V _{GS} =0	-60			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-14A	18	26		S

Marking : J652

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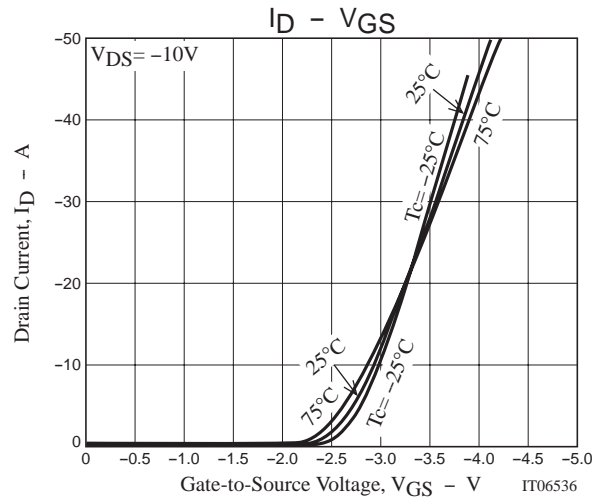
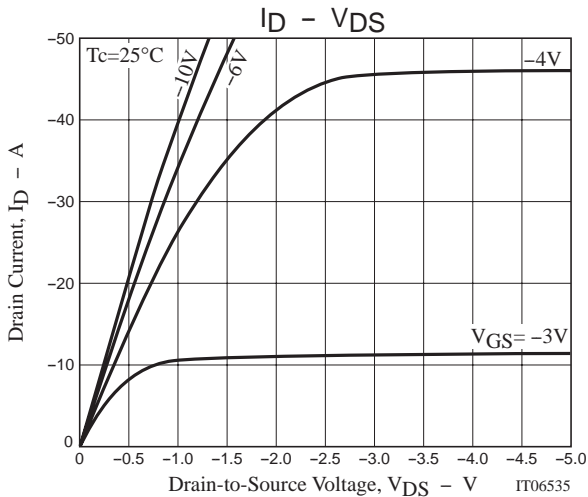
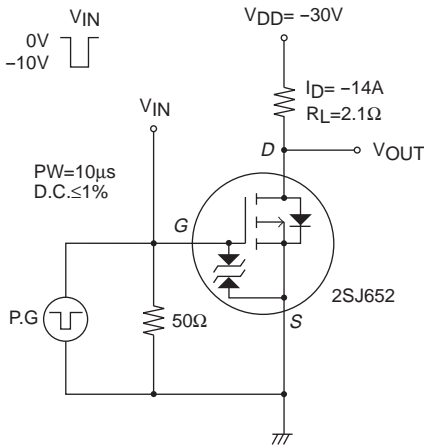
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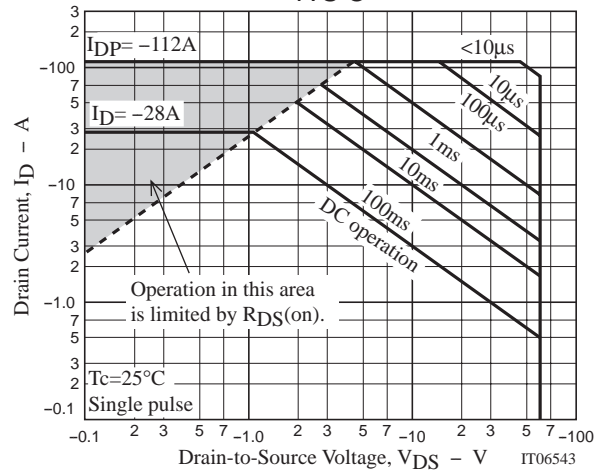
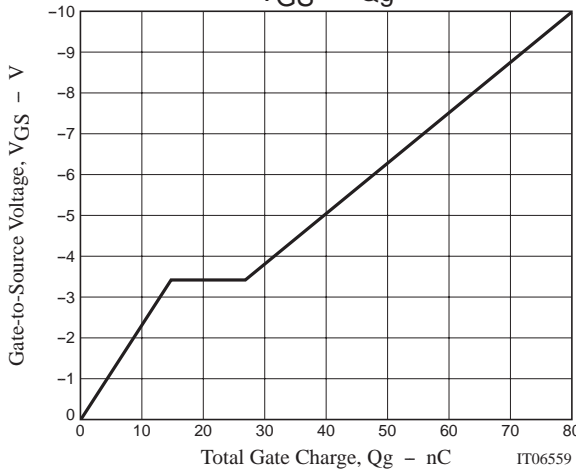
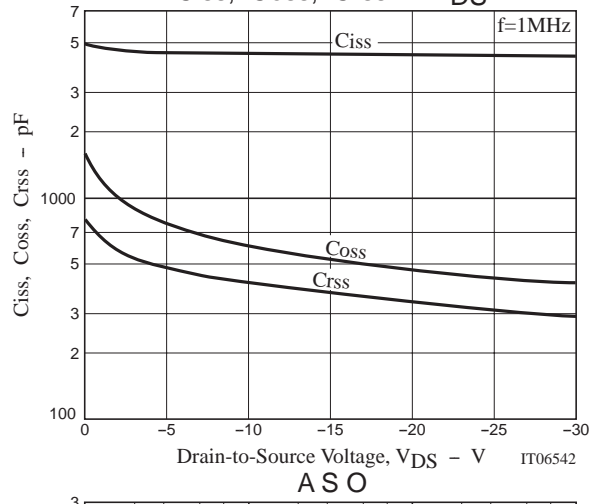
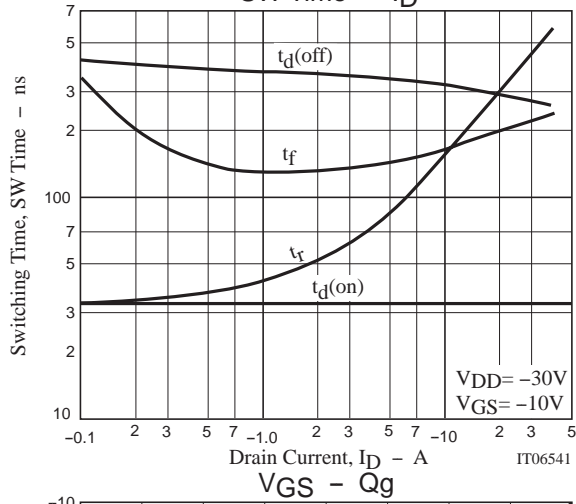
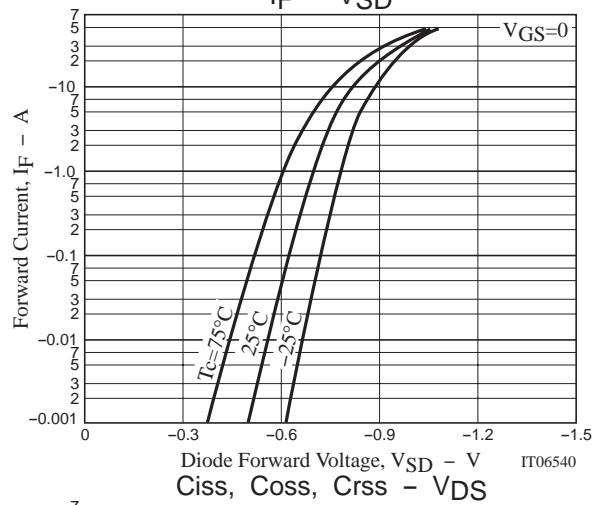
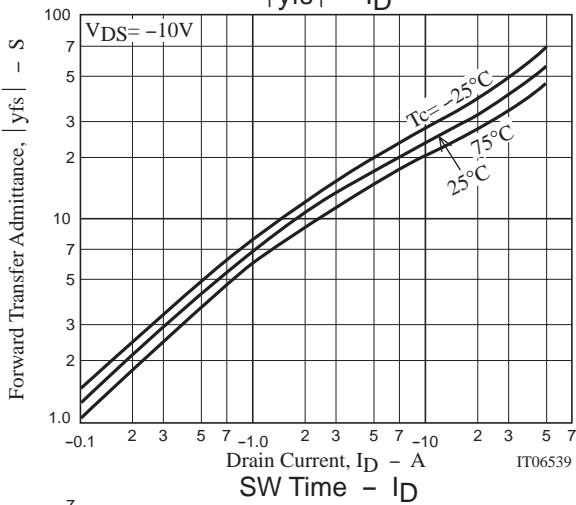
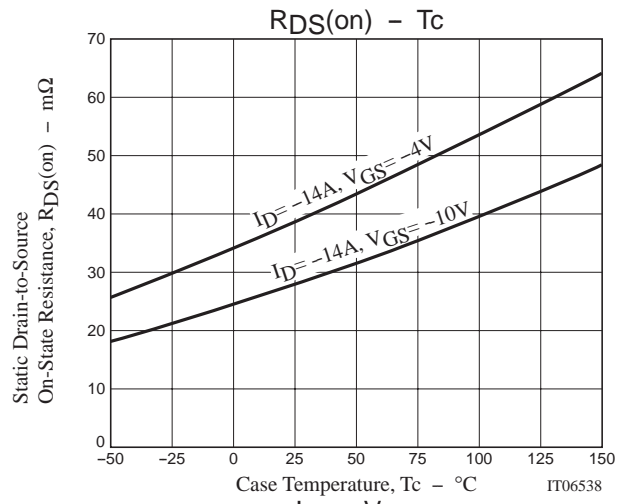
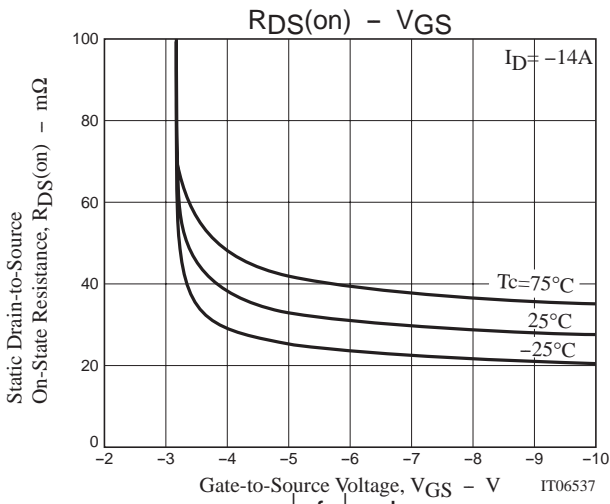
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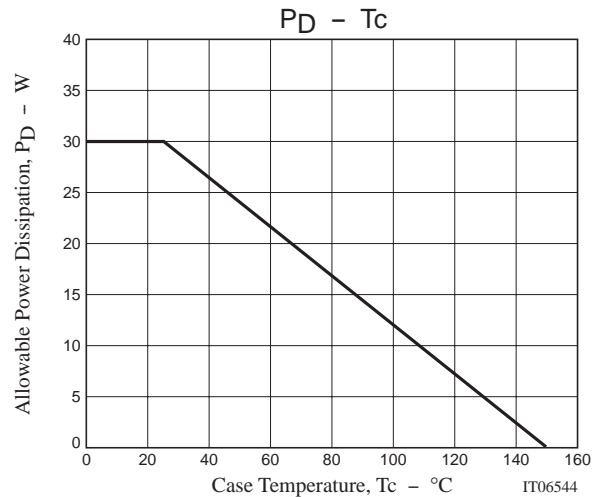
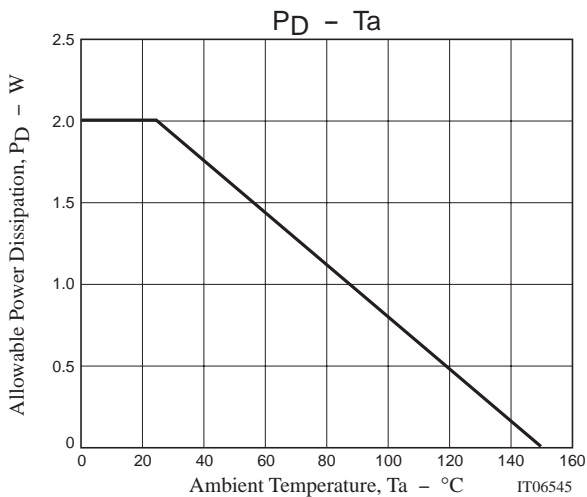
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -14A, V_{GS} = -10V$		28.5	38	m Ω
	$R_{DS(on)2}$	$I_D = -14A, V_{GS} = -4V$		39	55.5	m Ω
Input Capacitance	C_{iss}	$V_{DS} = -20V, f = 1MHz$		4360		pF
Output Capacitance	C_{oss}	$V_{DS} = -20V, f = 1MHz$		470		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20V, f = 1MHz$		335		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		33		ns
Rise Time	t_r	See specified Test Circuit.		210		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		310		ns
Fall Time	t_f	See specified Test Circuit.		180		ns
Total Gate Charge	Q_g	$V_{DS} = -30V, V_{GS} = -10V, I_D = -28A$		80		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS} = -30V, V_{GS} = -10V, I_D = -28A$		15		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS} = -30V, V_{GS} = -10V, I_D = -28A$		12		nC
Diode Forward Voltage	V_{SD}	$I_S = -28A, V_{GS} = 0$		-0.96	-1.2	V

Switching Time Test Circuit



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